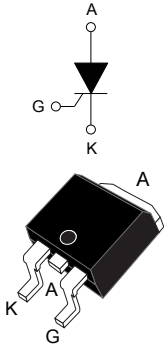



## 40 A 1200 V automotive grade thyristor (SCR) in D<sup>2</sup>PAK package



### Features

- AEC-Q101 qualified 
- Max. blocking voltage =  $V_{DRM}$ ,  $V_{RRM} = 1200\text{ V}$
- Max. surge voltage =  $V_{DSM}$ ,  $V_{RSM} = 1400\text{ V}$
- Nominal RMS on-state current:  $40\text{ A}_{RMS}$
- Max. junction temperature:  $150\text{ °C}$
- Maximum  $I_{GT} = 50\text{ mA}$
- High dynamic performances at  $T_J = 150\text{ °C}$ 
  - Off state  $dV/dt = 1500\text{ V}/\mu\text{s}$
  - Turn on  $dI/dt = 200\text{ A}/\mu\text{s}$
- ECOPACK2 compliant component
  - RoHS
  - Halogen Free molding compound

#### Product status

TN4050HA-12GY

#### Product summary

$I_{T(RMS)}$	40 A
$V_{DRM}/V_{RRM}$	1200 V
$V_{DSM}/V_{RSM}$	1400 V
$I_{GT}$	50 mA
$T_J$	-40 to $150\text{ °C}$

### Application

- Off and on board charger
- Renewable energy inverters
- Uninterruptible power supply (UPS)
- Capacitor discharge
- Crowbar / fast discharge circuit
- Bypass solid state relay (SSR)
- AC DC inrush current limiter (ICL)
- AC DC voltage-controlled rectifier
- AC motor soft starter

### Description

The **TN4050HA-12GY**, rated 40 A RMS current, offers superior performance in peak voltage robustness up to 1400 V and surge current handling up to 400 A 10 ms sine wave pulse.

Its key features allow the design of functions such as a 55 A RMS AC switch, dual back-to-back SCRs, and a 50 A average AC-DC controlled bridge rectifier for inrush current limitation, among other applications.

This SCR is an automotive grade thyristor designed for applications such as automotive on-board chargers, solid state relays, and stationary battery chargers where high off state immunity is required.

Available in D<sup>2</sup>PAK package, it is ideal for higher power compact SMD design on printed circuit board or insulated metal substrate board.

# 1 Characteristics

**Table 1. Absolute ratings (limiting values)**

Symbol	Parameter		Value	Unit	
$I_{T(RMS)}$	RMS on-state current (180 ° conduction angle)		40	A	
$I_{T(AV)}$	Average on-state current (180 ° conduction angle)				
$I_{TSM}$	Non repetitive surge peak on-state current, $V_R = 0$ V	$t_p = 8.3$ ms	438	A	
		$t_p = 10$ ms			
$I^2t$	$I^2t$ value for fusing	$t_p = 10$ ms	800	$A^2s$	
$di/dt$	Critical rate of rise of on-state current, $I_G = 2 \times I_{GT}$ , $t_r \leq 100$ ns	$f = 50$ Hz	200	$A/\mu s$	
$V_{DRM} / V_{RRM}$	Repetitive peak off-state voltage (50-60 Hz)		$T_j = -40$ to $+125$ °C	1200	V
			$T_j = -40$ to $+150$ °C	800	
$V_{DSM} / V_{RSM}$	Non repetitive surge peak off-state voltage	$t_p = 10$ ms	1400	V	
$V_{GM}$	Peak forward gate voltage	$t_p = 20$ $\mu s$	5	V	
$I_{GM}$	Peak forward gate current			8	A
$V_{RGM}$	Maximum peak reverse gate voltage		3.5	V	
$P_{G(AV)}$	Average gate power dissipation		1	W	
$T_{stg}$	Storage junction temperature range			-40 to +150 °C	
$T_j$	Operating junction temperature				

**Table 2. Electrical characteristics ( $T_j = 25$  °C unless otherwise specified)**

Symbol	Test Conditions		Value	Unit	
$I_{GT}$	$V_D = 12$ V, $R_L = 33$ $\Omega$	Min.	10	mA	
		Max.	50		
$V_{GT}$		Max.	1.3	V	
$V_{GD}$	$V_D = 800$ V, $R_L = 3.3$ k $\Omega$	$T_j = 150$ °C	Min.	0.2	V
$I_{GD}$	$V_D = 800$ V, $R_L = 3.3$ k $\Omega$	$T_j = 150$ °C	Min.	2.5	mA
$I_H$	$I_T = 500$ mA, gate open		Max.	100	mA
$I_L$	$I_G = 1.2 \times I_{GT}$		Max.	125	mA
$dV/dt$	$V_D = 800$ V, gate open	$T_j = 125$ °C	Min.	3000	$V/\mu s$
		$T_j = 150$ °C	Min.	1500	

**Table 3. Timing Parameters**

Symbol	Test Conditions		Value	Unit	
$t_{gt}$	$I_T = 40$ A, $V_D = 800$ V, $I_G = 2 \times I_{GT}$ , $di_G/dt = 0.2$ A/ $\mu s$	$T_j = 25$ °C	Typ.	2	$\mu s$
$t_q$	$I_T = 40$ A, $V_D = 800$ V, $(di/dt)_{OFF} = 10$ A/ $\mu s$ , $V_R = 75$ V, $dV_D/dt = 20$ V/ $\mu s$ , $t_p = 100$ $\mu s$	$T_j = 150$ °C	Typ.	150	$\mu s$

**Table 4. Static Characteristics**

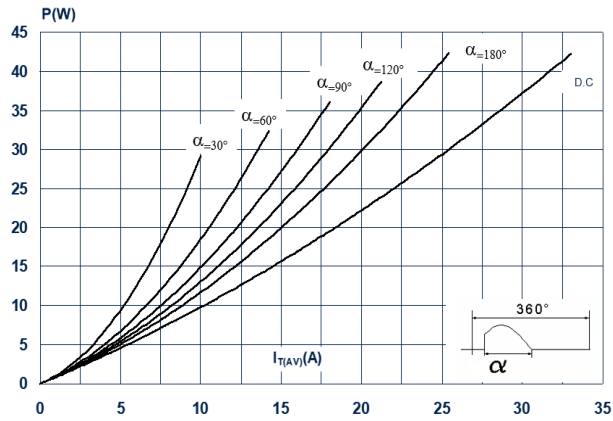
Symbol	Test Conditions			Value	Unit
$V_{TM}$	$I_{TM} = 50 \text{ A}$ , $t_p = 380 \text{ } \mu\text{s}$	$T_j = 25 \text{ }^\circ\text{C}$	Max.	1.55	V
$V_{TO}$	On-state threshold voltage	$T_j = 150 \text{ }^\circ\text{C}$	Max.	0.85	V
$R_D$	On-state dynamic resistance	$T_j = 150 \text{ }^\circ\text{C}$	Max.	13	m $\Omega$
$I_{DRM}/I_{RRM}$	$V_D = V_R = 1200 \text{ V}$	$T_j = 25 \text{ }^\circ\text{C}$	Max.	3	$\mu\text{A}$
		$T_j = 125 \text{ }^\circ\text{C}$		3	mA
	$V_D = V_R = 800 \text{ V}$	$T_j = 150 \text{ }^\circ\text{C}$		10	mA
$I_{DSM}/I_{RSM}$	$V_D = V_R = 1400 \text{ V}$	$T_j = 25 \text{ }^\circ\text{C}$	Max.	10	$\mu\text{A}$

**Table 5. Thermal parameters**

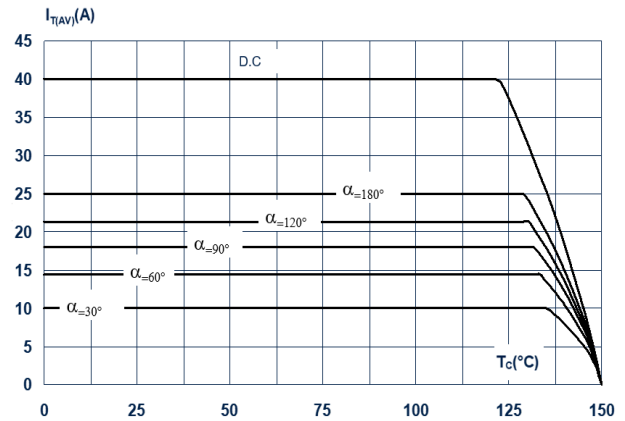
Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Thermal resistance junction to case (DC)	Max.	0.5
$R_{th(j-a)}$	Junction to ambient, (DC, $S_{CU} = 2.5 \text{ cm}^2$ , $e_{CU} = 70 \text{ } \mu\text{m}$ )	Typ.	45

## 1.1 Characteristics (curves)

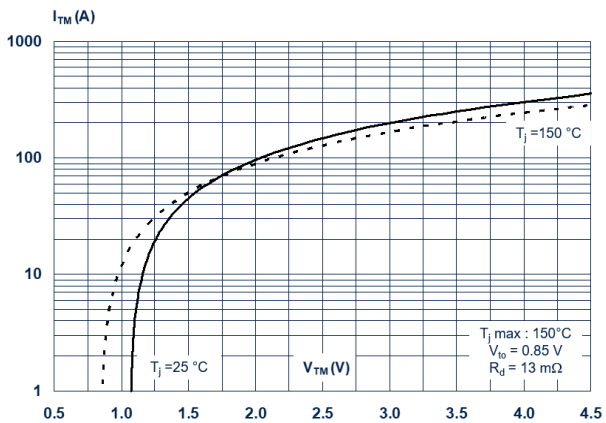
**Figure 1. Maximum average power dissipation versus average on-state current**



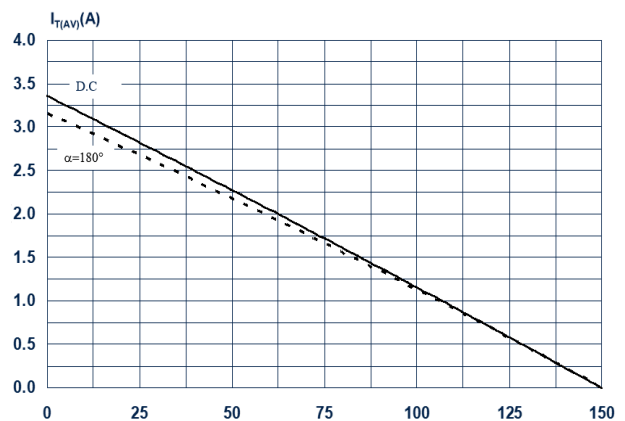
**Figure 2. Average and D.C. on-state current versus case temperature**



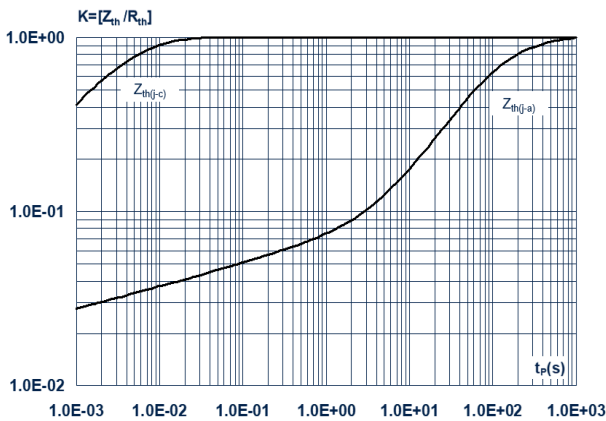
**Figure 3. On-state characteristics (maximum values)**



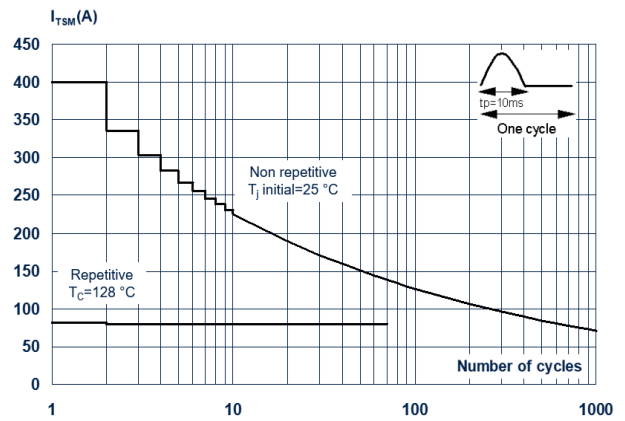
**Figure 4. Average and D.C. on-state current versus ambient temperature**



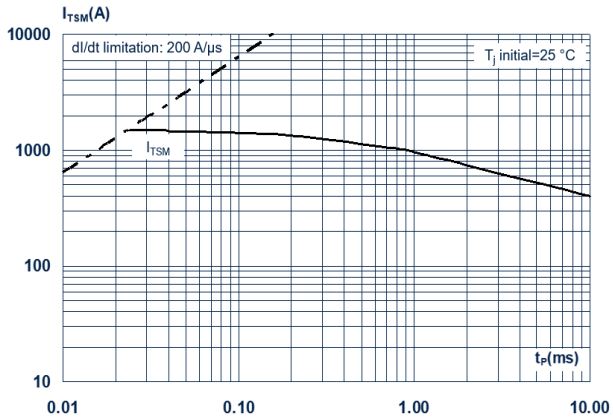
**Figure 5. Relative variation of thermal impedance junction to case and junction to ambient versus pulse duration**



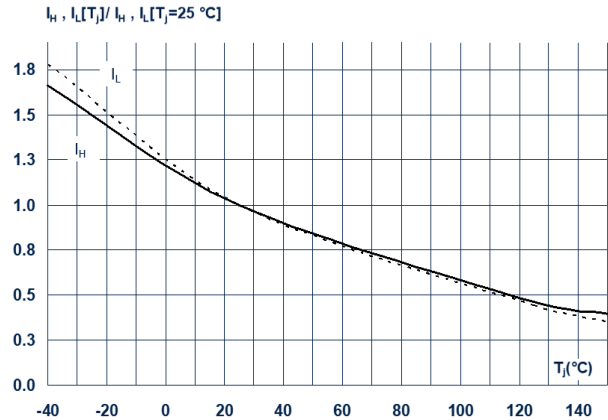
**Figure 6. Surge peak on-state current versus number of cycles (V\_R = 0 V)**



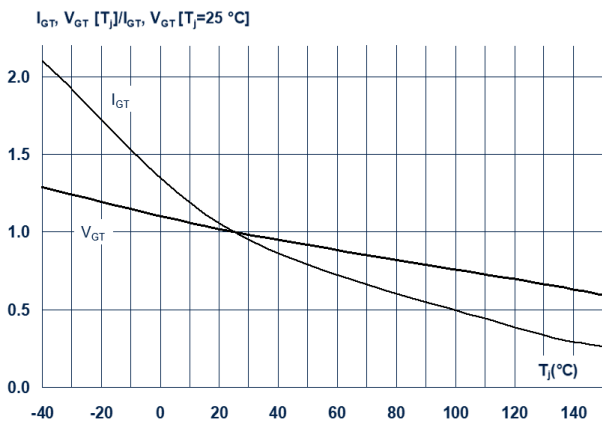
**Figure 7. Non repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 10$  ms ( $V_R = 0$  V)**



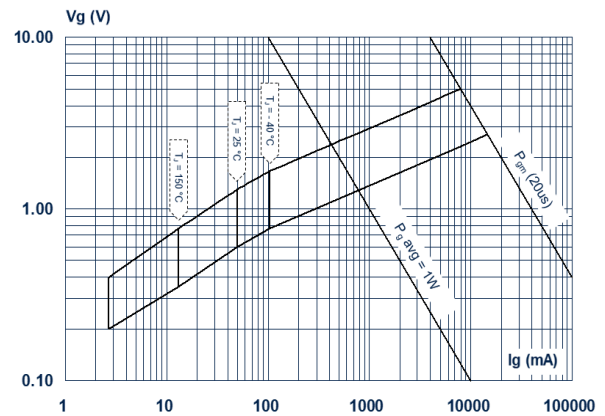
**Figure 8. Relative variation of holding and latching current versus junction temperature (typical values)**



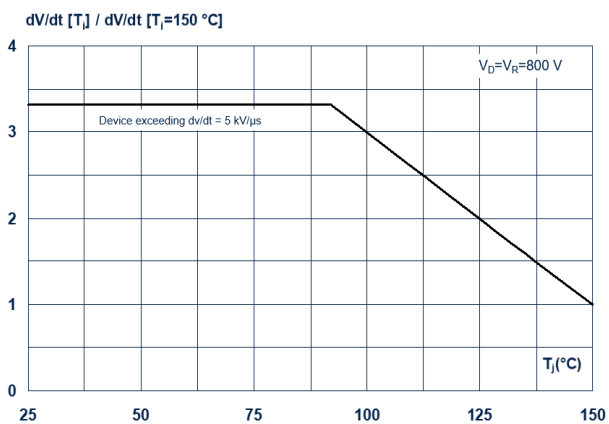
**Figure 9. Relative variation of gate trigger current and gate voltage versus junction temperature (typical values)**



**Figure 10. Gate characteristics, voltage versus current**



**Figure 11. Relative variation of static  $dv/dt$  immunity versus junction temperature**



**Figure 12. Relative variation of leakage current versus junction temperature for different values of blocking voltage (typical values)**

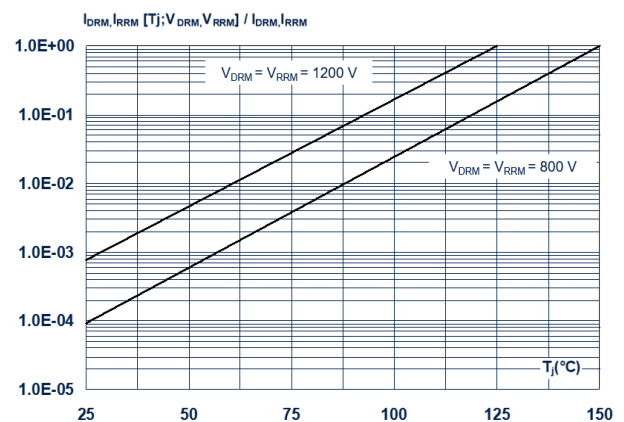
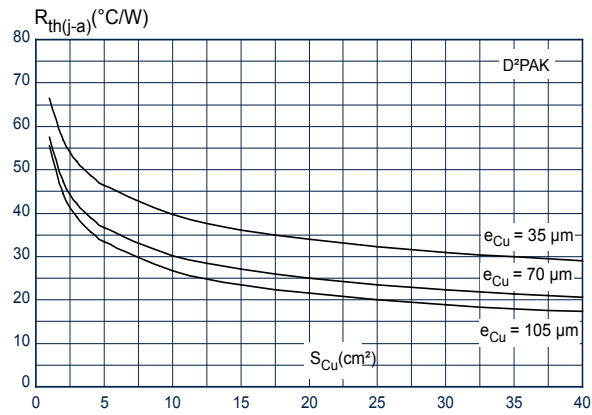


Figure 13. Thermal resistance junction to ambient versus copper surface under tab (typical values, epoxy printed board FR4) (D<sup>2</sup>PAK)



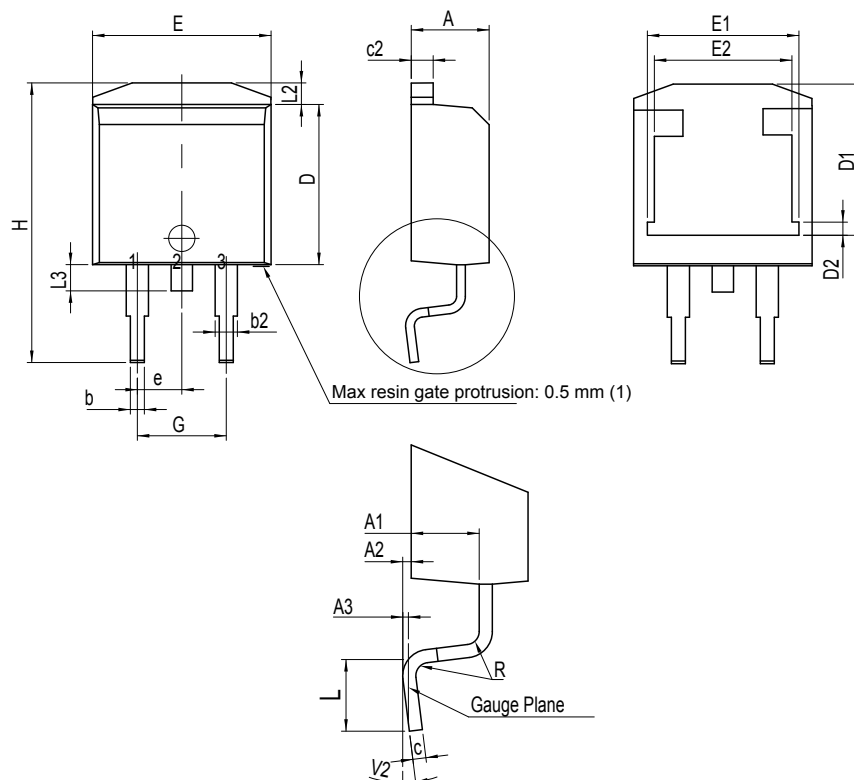
## 2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

### 2.1 D<sup>2</sup>PAK package information

- Molding compounded resin is halogen free and meets UL94 flammability standard, level V0
- Lead-free package leads plating

Figure 14. D<sup>2</sup>PAK package outline



(1) Resin gate is accepted in each of position shown on the drawing, or their symmetrical.

**Table 6. D<sup>2</sup>PAK package mechanical data**

Ref.	Dimensions					
	Millimeters			Inches <sup>(1)</sup>		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.30		4.60	0.1693		0.1811
A1	2.49		2.69	0.0980		0.1059
A2	0.03		0.23	0.0012		0.0091
A3		0.25			0.0098	
b	0.70		0.93	0.0276		0.0366
b2	1.25		1.7	0.0492		0.0669
c	0.45		0.60	0.0177		0.0236
c2	1.21		1.36	0.0476		0.0535
D	8.95		9.35	0.3524		0.3681
D1	7.50		8.00	0.2953		0.3150
D2	1.30		1.70	0.0512		0.0669
e		2.54			0.1	
E	10.00		10.28	0.3937		0.4047
E1	8.30		8.70	0.3268		0.3425
E2	6.85		7.25	0.2697		0.2854
G	4.88		5.28	0.1921		0.2079
H	15		15.85	0.5906		0.6240
L	1.78		2.28	0.0701		0.0898
L2	1.19		1.40	0.0470		0.0551
L3	1.40		1.75	0.0551		0.0689
R		0.40			0.0157	
V2	0°		8°	0°		8°

1. Dimensions in inches are given for reference only

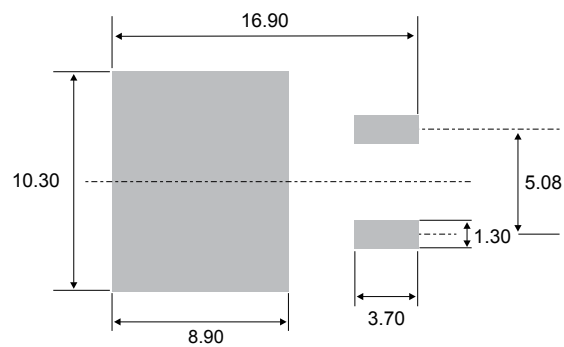
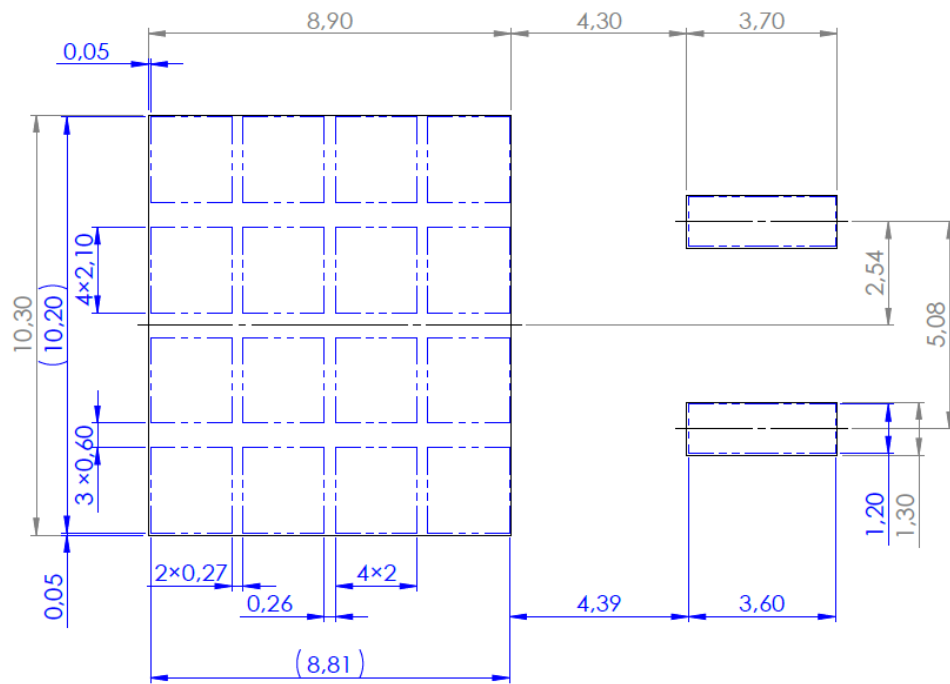
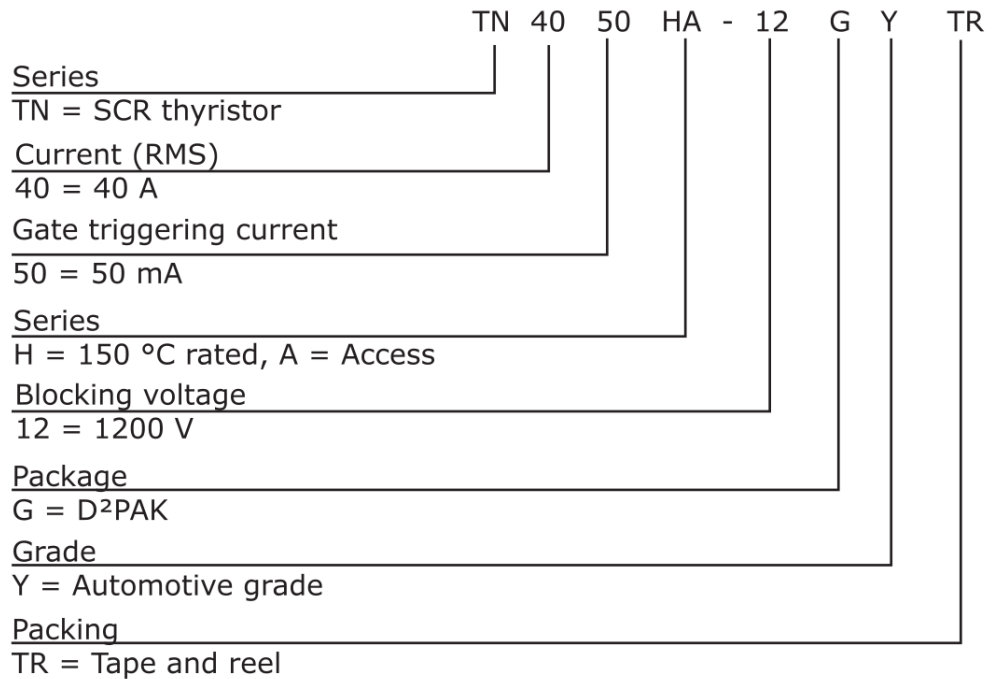
**Figure 15. D<sup>2</sup>PAK recommended footprint (dimensions are in mm)**




Figure 16. D<sup>2</sup>PAK stencil definitions (dimensions are in mm)



### 3 Ordering information

**Figure 17. Ordering information scheme**

**Table 7. Ordering information**

Order code	Marking	Package	Weight	Base qty.	Delivery mode
TN4050HA-12GY-TR	TN4050HA12GY	D <sup>2</sup> PAK	1.38 g	1000	Tape and reel
TN4050HA-12GY	TN4050HA12GY			50	Tube

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## Revision history

**Table 8. Document revision history**

Date	Revision	Changes
29-Jun-2022	1	Initial release.

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